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GaAs Etching using Panasonic ICP Etcher#2											
Sample	Bias (W)	ICP (W)	Pressure (Pa)	Gas Flow-Rate (sccm)		Etch Time (min.)	Average Etch Depth (nm)	Average SiO_2 Thickness (nm)	Etch Rate (nm/min.)	Selectivity ($GaAs/SiO_2$)	Average Side-wall Angle (°)
				Cl_2	N_2						
GaAs_02	100	900	0.2	20	10	3	1740	346.0	565.0	11.8	90
GaAs_04	75	900	0.2	15	10	3	1255	398.5	403.3	13.2	90

Figure 1 (a) GaAs etch profile of GaAs_02; (b) GaAs etch profile of GaAs_04.